

# **Product Change Notice (PCN)**

Subject: Datasheet specification change for listed Renesas HIP4020\* Products Publication Date: 2/11/2019 Effective Date: 5/12/2019

## **Revision Description:**

Initial Release

# **Description of Change:**

This notice is to inform you that Renesas Electronics America Inc has updated datasheet. The update includes a change to the following electrical parameter: -

Γ		Maximu	Maximum Limit	
#	Change details	From	То	Unit
1	P-channel r <sub>DS</sub> (ON), Low Supply Voltage	2.1	2.5	Ω

## Affected Product List

HIP4020IBZ
HIP4020IBZT
HIP4020IBZTS2705

# Reason for Change:

The change to the datasheet aligns the documentation with the product characteristics and is necessary to maintain product manufacturability in support of customer delivery requirements. Details regarding the change are contained on the following page. The product datasheet is available on the Renesas website at : -

https://www.renesas.com/sg/en/www/doc/datasheet/hip4020.pdf

# Impact on fit, form, function, quality & reliability:

The change will have no other impact on the form, fit, function, quality, reliability and environmental compliance of the devices.

# Product Identification:

Product affected by this change is identifiable via Renesas's internal traceability system.

Qualification status: Not Applicable Sample availability: 2/18/2019 Device material declaration: Available upon request

Questions or requests pertaining to this change notice, including additional data or samples, must be sent to Renesas within 30 days of the publication date.

 For additional information regarding this notice, please contact your regional change coordinator (below)

 Americas: PCN-US@RENESAS.COM
 Europe: PCN-EU@RENESAS.COM
 Japan: PCN-JP@RENESAS.COM
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#### Appendix A – Affected datasheet (see attached)

#### HIP4020\* datasheet

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## **Electrical Specifications** $T_A = 25^{\circ}C$ , $V_{DD} = +5V$ , $V_{SSA} = V_{SSB} = V_{SS} = 0V$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Input Leakage Current	ILEAK	V <sub>DD</sub> = +15V	-	-	25	nA
Low Level Input Voltage	V <sub>IL</sub>		VSS	-	0.8	V
High Level Input Voltage	VIH		2		V <sub>DD</sub>	V
ILF Output Low, Sink Current	ЮН	V <sub>OUT</sub> = 0.4V, V <sub>DD</sub> = +12V	15	2	2	mA
ILF Output High, Source Current	OL	V <sub>OUT</sub> = 11.6V, V <sub>DD</sub> = +12V		12	-15	mA
Input Capacitance	CIN		100	2	-	pF
P-Channel rDS(ON), Low Supply Voltage	rDS(ON)	V <sub>DD</sub> = +3V, I <sub>SOURCE</sub> = 250mA		1.6	2.1	Ω

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#### **Electrical Specifications** $T_A = 25^{\circ}C$ , $V_{DD} = +5V$ , $V_{SSA} = V_{SSB} = V_{SS} = 0V$ , unless otherwise specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Leakage Current	ILEAK	V <sub>DD</sub> = +15V		-	25	nA
Low Level Input Voltage	VIL		VSS	-	0.8	V
High Level Input Voltage	VIH		2		V <sub>DD</sub>	V
ILF Output Low, Sink Current	I <sub>OH</sub>	V <sub>OUT</sub> = 0.4V, V <sub>DD</sub> = +12V	15	12	2	mA
ILF Output High, Source Current	IOL	V <sub>OUT</sub> = 11.6V, V <sub>DD</sub> = +12V	-		-15	mA
Input Capacitance	CIN			2		pF
P-Channel r <sub>DS(ON)</sub> , Low Supply Voltage	<sup>r</sup> DS(ON)	V <sub>DD</sub> = +3V, I <sub>SOURCE</sub> = 250mA	-	1.6	2.5	Ω